

N-channel TrenchMOS logic level FET Rev. 04 — 31 May 2010

**Product data sheet** 

#### **Product profile** 1.

#### 1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

#### 1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant

### 1.3 Applications

- 12 V and 24 V loads
- Automotive and general purpose power switching

### 1.4 Quick reference data

#### Table 1. Quick reference data

Table 1.	Quick reference da	lla					
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	55	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 5 V; T <sub>j</sub> = 25 °C; see <u>Figure 3</u> ; see <u>Figure 1</u>	[1]	-	-	75	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	-	300	W
Static cha	racteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \ V; \ I_{D} = 25 \ A; \\ T_{j} = 25 \ ^{\circ}C \end{array}$		-	4.8	5.8	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}$		-	-	6.7	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C};$ see <u>Figure 12</u> ; see <u>Figure 13</u>		-	5.3	6.3	mΩ
Avalanch	e ruggedness						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D = 75 \text{ A}; V_{sup} \le 55 \text{ V};$ $R_{GS} = 50 \Omega; V_{GS} = 5 \text{ V};$ $T_{j(init)} = 25 ^{\circ}\text{C}; \text{ unclamped}$		-	-	1.1	J

- Suitable for logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating
- Motors, lamps and solenoids

# nexperia

[1] Continuous current is limited by package.

# 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT226 (I2PAK)	

# 3. Ordering information

Table 3. Ordering	information		
Type number	Package		
	Name	Description	Version
BUK9E06-55A	I2PAK	plastic single-ended package (I2PAK); TO-262	SOT226

# 4. Limiting values

#### Table 4. Limiting values

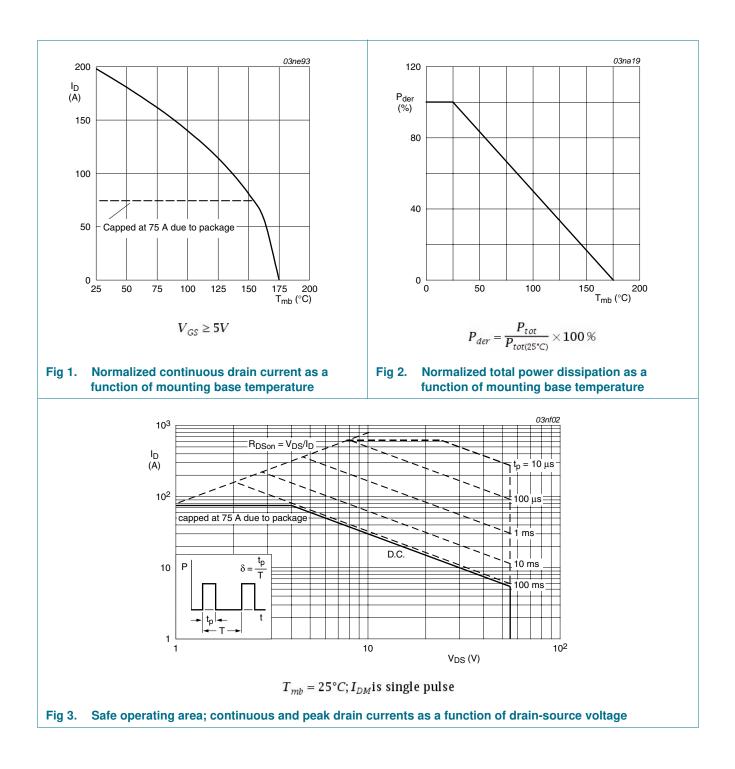
In accordance with the Absolute Maximum Rating System (IEC 60134).

0	B				-		11.24
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	55	V
V <sub>DGR</sub>	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$		-	-	55	V
V <sub>GS</sub>	gate-source voltage			-15	-	15	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 5 V; T <sub>j</sub> = 25 °C;	[1]	-	-	154	А
		see <u>Figure 3</u> ; see <u>Figure 1</u>	[2]	-	-	75	А
		$V_{GS}$ = 5 V; $T_j$ = 100 °C; see <u>Figure 1</u>	[2]	-	-	75	А
I <sub>DM</sub>	peak drain current	$T_{mb} = 25 \text{ °C}; t_p \le 10 \mu\text{s}; \text{ pulsed};$ see <u>Figure 3</u>		-	-	616	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	-	300	W
T <sub>stg</sub>	storage temperature			-55	-	175	°C
Tj	junction temperature			-55	-	175	°C
Source-drain	diode						
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	-	154	А
			[2]	-	-	75	А
I <sub>SM</sub>	peak source current	$t_p \le 10 \ \mu s$ ; pulsed; $T_{mb} = 25 \ ^{\circ}C$		-	-	616	А
Avalanche ru	Iggedness						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$    I_D = 75 \text{ A};  \text{V}_{\text{sup}} \leq 55 \text{ V};  \text{R}_{\text{GS}} = 50  \Omega; \\ \text{V}_{\text{GS}} = 5 \text{ V};  \text{T}_{j(\text{init})} = 25 ^{\circ}\text{C}; \text{ unclamped} $		-	-	1.1	J

[1] Current is limited by power dissipation chip rating.

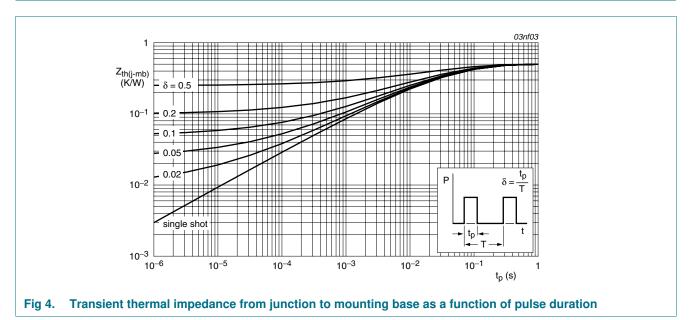
[2] Continuous current is limited by package.

# BUK9E06-55A



### 5. Thermal characteristics

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance from junction to mounting base	see <u>Figure 4</u>	-	-	0.5	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	vertical in still air	-	60	-	K/W



## 6. Characteristics

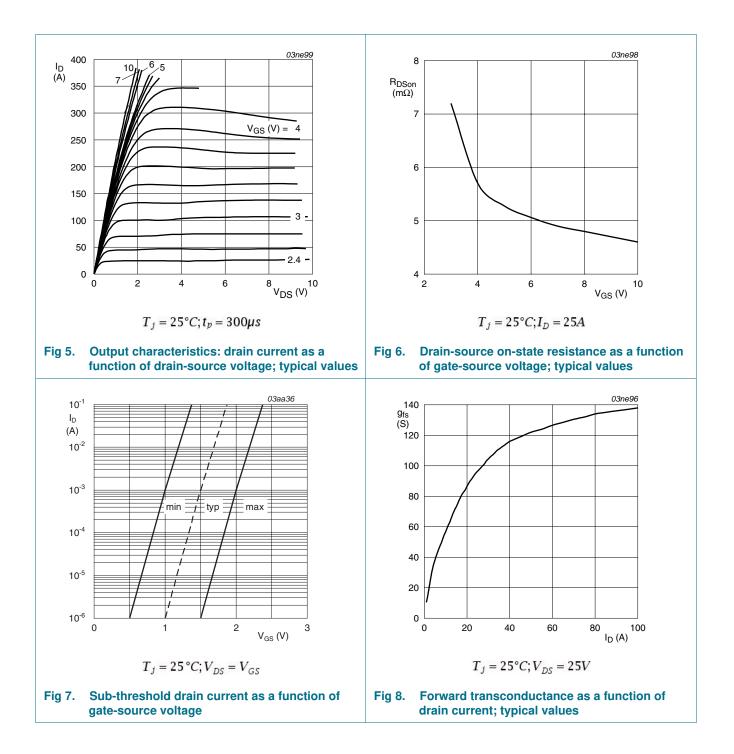
#### Table 6. **Characteristics** Symbol Parameter Conditions Min Тур Max Unit **Static characteristics** drain-source $I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$ 55 ٧ V<sub>(BR)DSS</sub> \_ breakdown voltage I<sub>D</sub> = 0.25 mA; V<sub>GS</sub> = 0 V; T<sub>i</sub> = -55 °C 50 V \_ \_ $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_i = 25 \text{ °C};$ 1 1.5 2 ٧ V<sub>GS(th)</sub> gate-source threshold voltage see Figure 11 $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ ٧ 2.3 -see Figure 11 $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_i = 175 \text{ °C};$ V 0.5 -\_ see Figure 11 $V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_{j} = 175 \text{ °C}$ drain leakage current 500 μΑ IDSS -- $V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_{j} = 25 \text{ °C}$ -0.05 10 μΑ $V_{DS} = 0 V; V_{GS} = 10 V; T_{j} = 25 °C$ gate leakage current 2 100 nA I<sub>GSS</sub> -V<sub>DS</sub> = 0 V; V<sub>GS</sub> = -10 V; T<sub>i</sub> = 25 °C 2 100 nA

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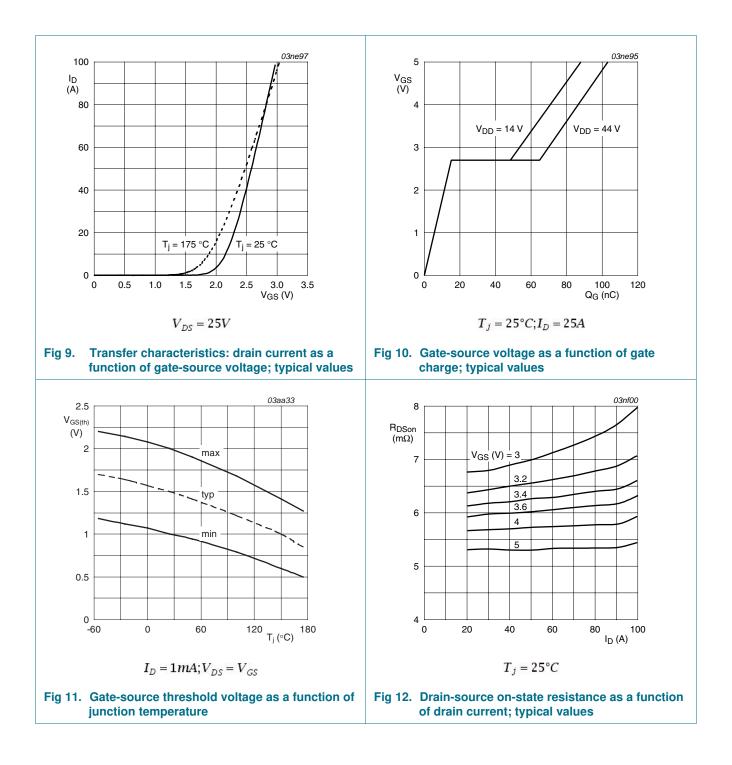
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 5 V; I <sub>D</sub> = 25 A; T <sub>i</sub> = 175 °C;	-	.,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	13.2	mΩ
USon	resistance	see Figure 12; see Figure 13	-	-	13.2	11122
		$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 25 °C	-	4.8	5.8	mΩ
		$V_{GS}$ = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C	-	-	6.7	mΩ
		V <sub>GS</sub> = 5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	5.3	6.3	mΩ
Dynamic ch	naracteristics					
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;$	-	6500	8600	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 14</u>	-	1000	1200	pF
C <sub>rss</sub>	reverse transfer capacitance		-	650	850	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 30 \text{ V}; \text{ R}_{L} = 1.2 \Omega; \text{ V}_{GS} = 5 \text{ V};$	-	45	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 10 \ \Omega; T_j = 25 \ ^{\circ}C$	-	180	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	420	-	ns
t <sub>f</sub>	fall time		-	235	-	ns
L <sub>D</sub>	internal drain inductance	from drain lead 6 mm from package to centre of die ; $T_j = 25 \text{ °C}$	-	4.5	-	nH
		from upper edge of drain mounting base to centre of die ; $T_j = 25 \text{ °C}$	-	2.5	-	nH
L <sub>S</sub>	internal source inductance	from source lead to source bond pad ; $T_j = 25 \ ^\circ C$	-	7.5	-	nH
Source-dra	in diode					
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 30 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; see <u>Figure 15</u>	-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{S} = 20 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s};$	-	80	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS} = -10 \text{ V};  V_{DS} = 30 \text{ V};  T_j = 25 ^{\circ}\text{C}$	-	200	-	nC

#### Table 6. Characteristics ...continued

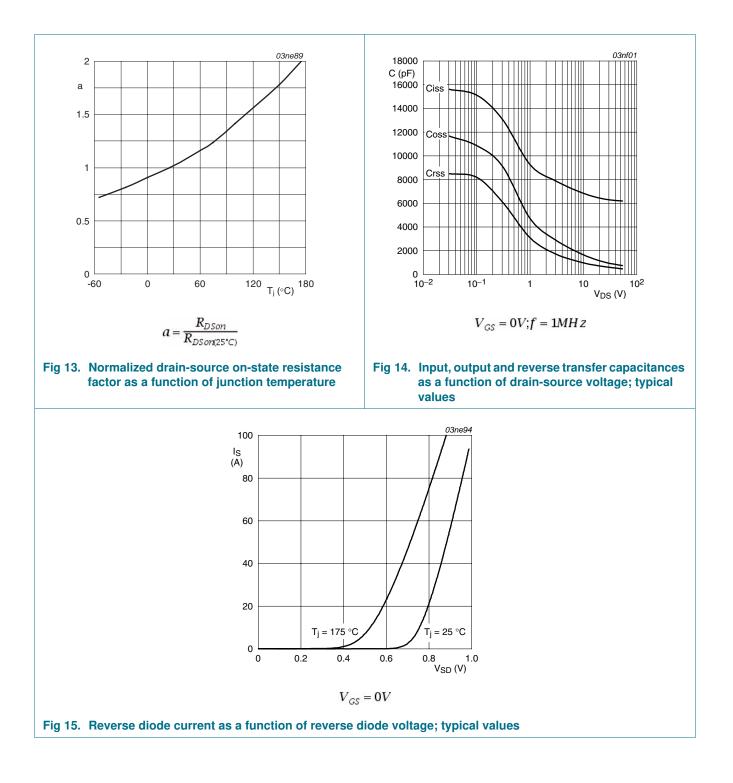
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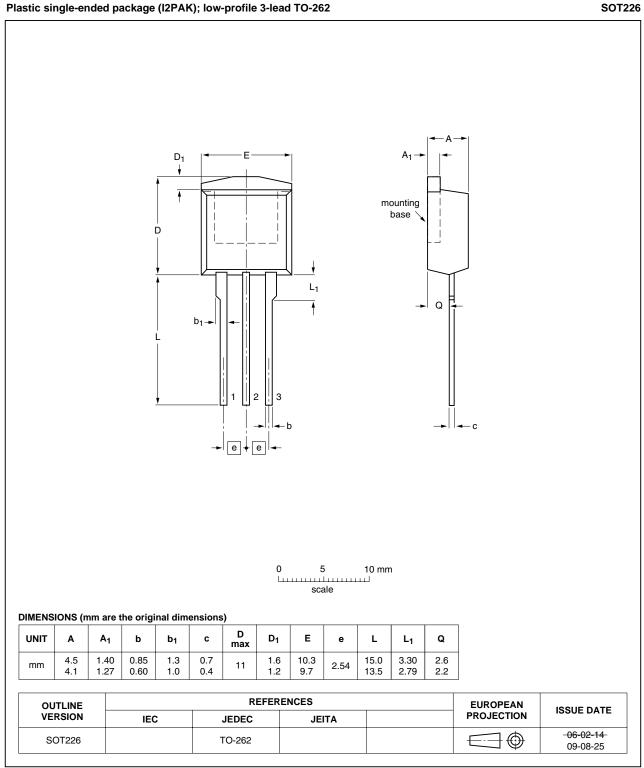


# BUK9E06-55A



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#### **Package outline** 7.



#### Fig 16. Package outline SOT226 (I2PAK)

BUK9E06-55A **Product data sheet**  **SOT226** 

# 8. Revision history

Table 7.Revision history				
Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK9E06-55A v.4	20100531	Product data sheet	-	BUK9506_9606_9E06_55A-03
Modifications:		t of this data sheet has of NXP Semiconductor	•	o comply with the new identity
	<ul> <li>Legal texts</li> </ul>	s have been adapted to	the new company	name where appropriate.
		ber BUK9E06-55A sepa _9606_9E06_55A-03.	rated from data sh	neet
BUK9506_9606_9E06_55A-03 (9397 750 08416)	20010723	Product data sheet	-	-

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## 9. Legal information

#### 9.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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